

Silicon Phototransistor in 0805 Package



20043-1

DESCRIPTION

TEMT7100X01 is a silicon NPN epitaxial planar phototransistor with daylight blocking filter in a miniature, black 0805 package for surface mounting. Filter bandwidth is matched with 830 nm to 950 nm IR emitters.

FEATURES

- Package type: surface mount
- Package form: 0805
- Dimensions (L x W x H in mm): 2 x 1.25 x 0.85
- AEC-Q101 qualified
- High photo sensitivity
- Daylight blocking filter matches with 830 nm to 950 nm IR emitters
- Angle of half sensitivity: $\varphi = \pm 60^\circ$
- Package matched with IR emitter series VSMB1940X01
- Floor life: 168 h, MSL 3, acc. J-STD-020
- Lead (Pb)-free reflow soldering
- Compliant to RoHS directive 2002/95/EC and in accordance to WEEE 2002/96/EC
- Find out more about Vishay's Automotive Grade Product requirements at: www.vishay.com/applications



APPLICATIONS

- Detector in automotive applications
- Photo interrupters
- Miniature switches
- Counters
- Encoders
- Position sensors

PRODUCT SUMMARY

COMPONENT	I _{caE} (μA)	φ (deg)	λ _{0.5} (nm)
TEMT7100X01	225 to 675	± 60	750 to 1010

Note

Test condition see table "Basic Characteristics"

ORDERING INFORMATION

ORDERING CODE	PACKAGING	REMARKS	PACKAGE FORM
TEMT7100X01	Tape and reel	MOQ: 3000 pcs, 3000 pcs/reel	0805

Note

MOQ: minimum order quantity

ABSOLUTE MAXIMUM RATINGS

PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
Collector emitter voltage		V _{CEO}	20	V
Emitter collector voltage		V _{ECO}	7	V
Collector current		I _C	20	mA
Power power dissipation	T _{amb} ≤ 55 °C	P _V	100	mW
Junction temperature		T _J	100	°C
Operating temperature range		T _{amb}	- 40 to + 100	°C
Storage temperature range		T _{stg}	- 40 to + 100	°C
Soldering temperature	Acc. reflow profile fig. 7	T _{sd}	260	°C
Thermal resistance junction/ambient	Acc. J-STD-051	R _{thJA}	270	K/W

Note

T_{amb} = 25 °C, unless otherwise specified

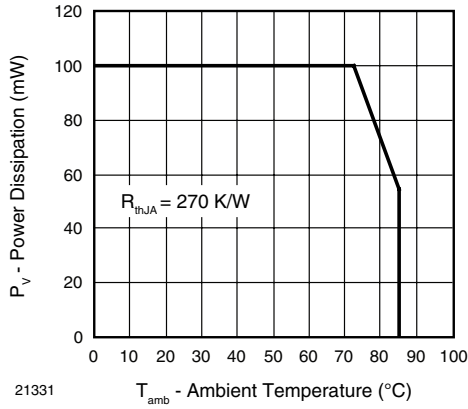


Fig. 1 - Power Dissipation Limit vs. Ambient Temperature

BASIC CHARACTERISTICS						
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Collector emitter breakdown voltage	$I_C = 0.1 \text{ mA}$	V_{CE0}	20			V
Collector dark current	$V_{CE} = 5 \text{ V}, E = 0$	I_{CE0}		1	100	nA
Collector emitter capacitance	$V_{CE} = 0 \text{ V}, f = 1 \text{ MHz}, E = 0$	C_{CEO}		25		pF
Collector light current	$E_e = 1 \text{ mW/cm}^2, \lambda = 950 \text{ nm}, V_{CE} = 5 \text{ V}$	I_{CA}	225	450	675	μA
Angle of half sensitivity		ϕ		± 60		deg
Wavelength of peak sensitivity		λ_p		870		nm
Range of spectral bandwidth		$\lambda_{0.5}$		750 to 1010		nm
Collector emitter saturation voltage	$I_C = 0.05 \text{ mA}$	V_{CEsat}			0.4	V

Note

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BASIC CHARACTERISTICS

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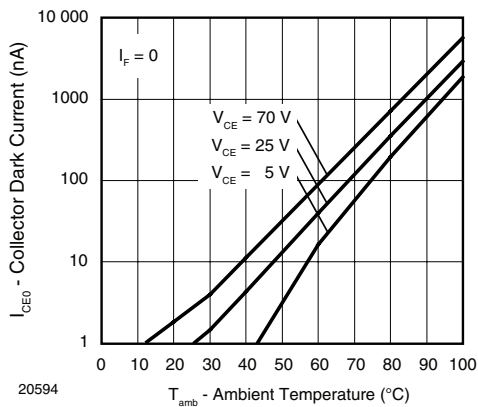


Fig. 2 - Collector Dark Current vs. Ambient Temperature

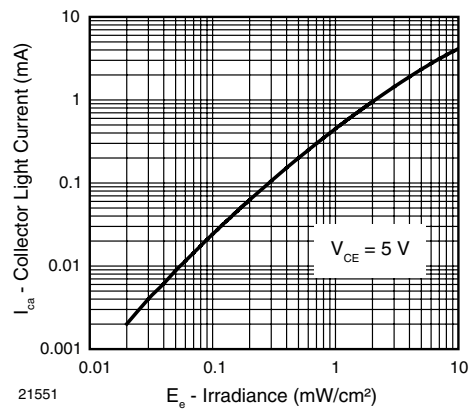


Fig. 3 - Collector Light Current vs. Irradiance

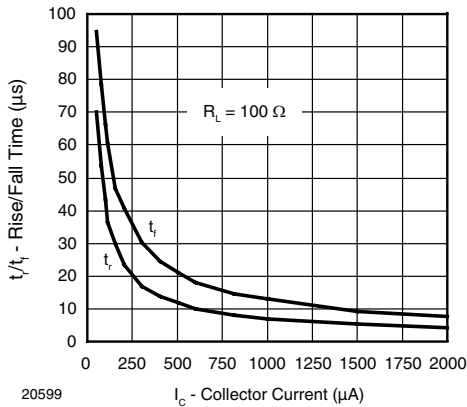


Fig. 4 - Rise/Fall Time vs. Collector Current

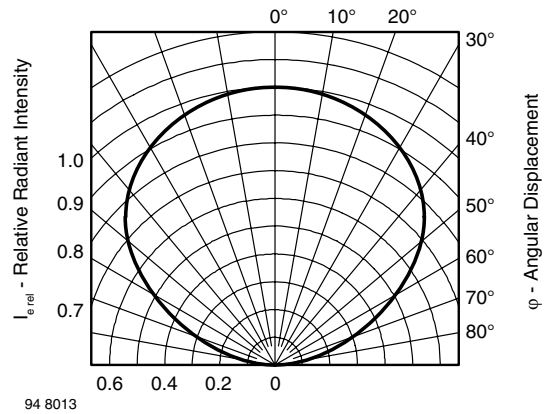


Fig. 6 - Relative Radiant Sensitivity vs. Angular Displacement

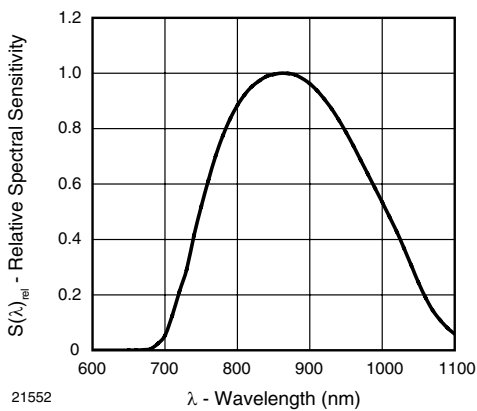


Fig. 5 - Relative Spectral Sensitivity vs. Wavelength

REFLOW SOLDER PROFILE

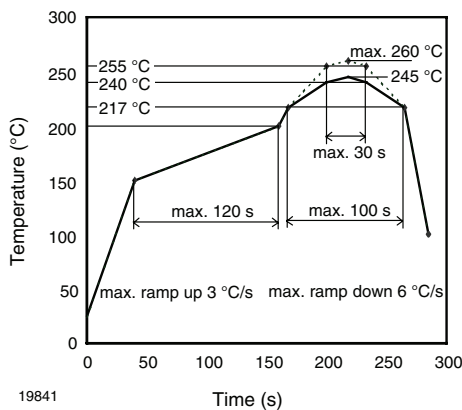


Fig. 7 - Lead (Pb)-free Reflow Solder Profile acc. J-STD-020D

DRYPACK

Devices are packed in moisture barrier bags (MBB) to prevent the products from moisture absorption during transportation and storage. Each bag contains a desiccant.

FLOOR LIFE

Floor life (time between soldering and removing from MBB) must not exceed the time indicated on MBB label:

Floor life: 168 h

Conditions: $T_{amb} < 30\text{ °C}$, $RH < 60\%$

Moisture sensitivity level 3, acc. to J-STD-020.

DRYING

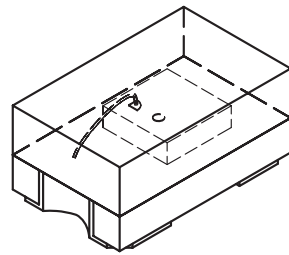
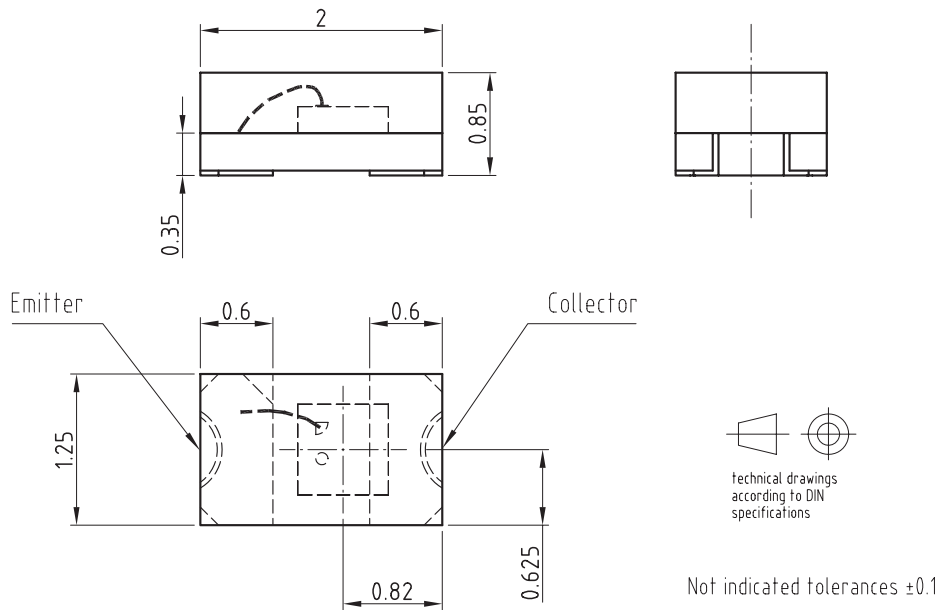
In case of moisture absorption devices should be baked before soldering. Conditions see J-STD-020 or label. Devices taped on reel dry using recommended conditions 192 h at $40\text{ °C} (+ 5\text{ °C})$, $RH < 5\%$.

TEMT7100X01

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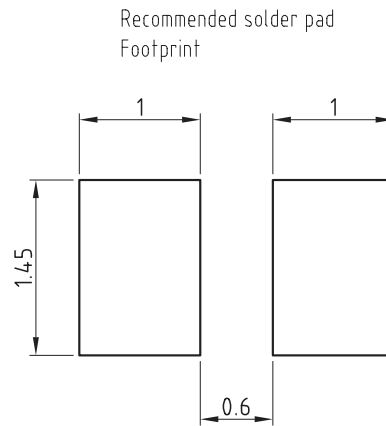


PACKAGE DIMENSIONS in millimeters

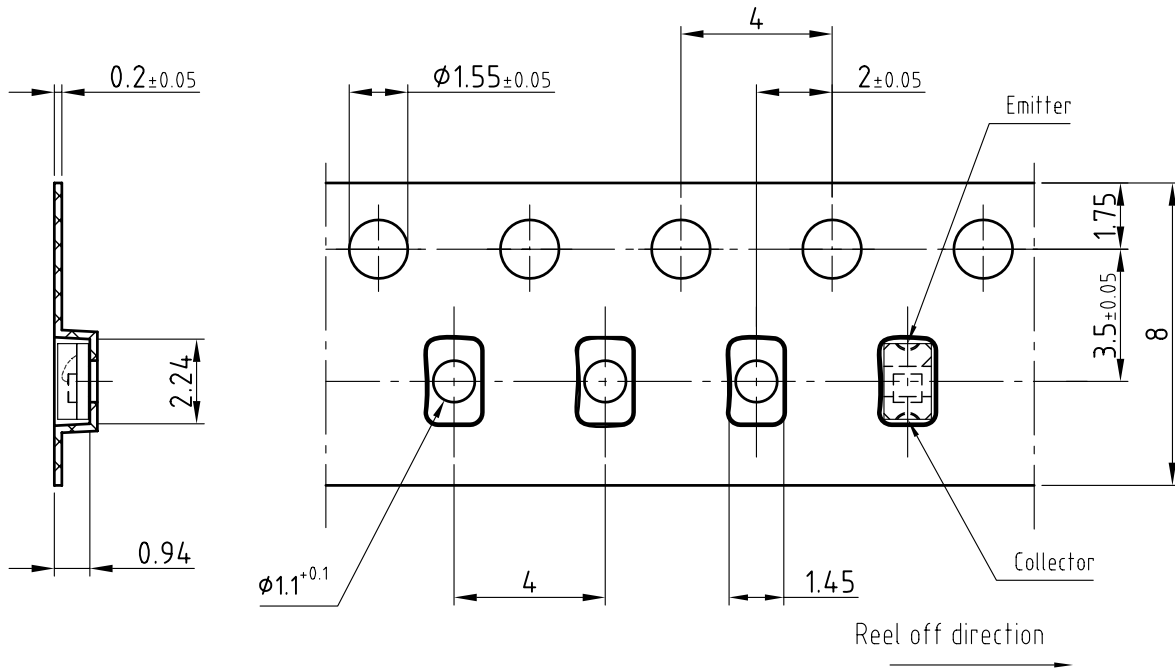


Drawing-No.: 6.541-5063.01-4
Issue: 3; 23.02.07

19757



BLISTER TAPE DIMENSIONS in millimeters



Drawing-No.: 9.700-5310.01-4
 Issue: 2; 14.08.07
 20690

Not indicated tolerances ± 0.1

Quantity per reel: 3000 pcs

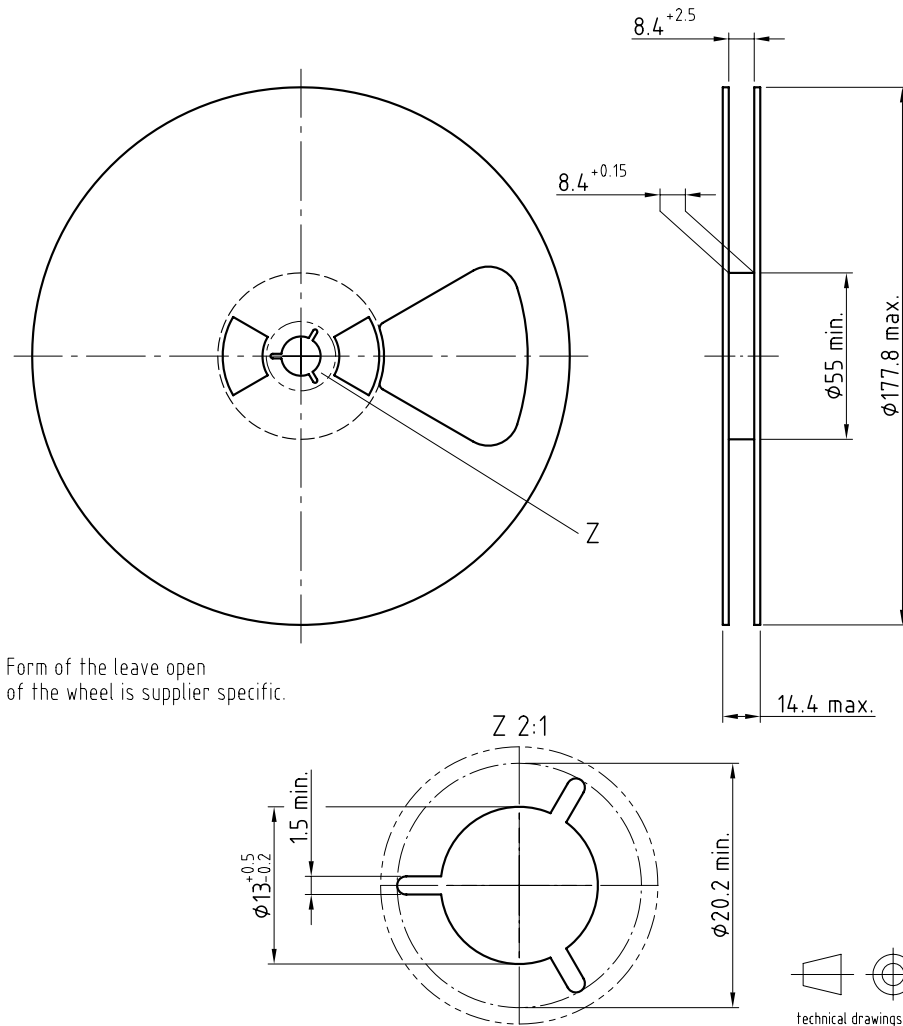
technical drawings according to DIN specifications

TEMT7100X01

Vishay Semiconductors Silicon Phototransistor in 0805 Package



REEL DIMENSIONS in millimeters



Drawing-No.: 9.800-5096.01-4

Issue: 1; 05.05.08

20875



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